

MMBT4126LT1G

General Purpose Transistor

PNP Silicon

Features

- Moisture Sensitivity Level: 1
- ESD Rating: – Human Body Model: > 4000 V
– Machine Model: > 400 V
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	–25	Vdc
Collector–Base Voltage	V_{CBO}	–25	Vdc
Emitter–Base Voltage	V_{EBO}	–4	Vdc
Collector Current–Continuous	I_C	–200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board (Note 1) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient (Note 1)	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient (Note 2)	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{stg}	–55 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

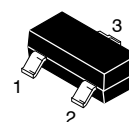
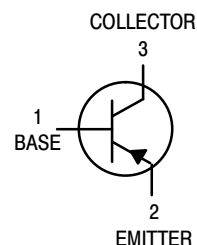
1. FR–5 = $1.0 \times 0.75 \times 0.062$ in.

2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



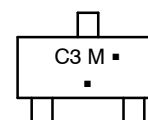
ON Semiconductor®

<http://onsemi.com>



SOT–23
CASE 318
STYLE 6

MARKING DIAGRAM



C3 = Device Code

M = Date Code*

▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBT4126LT1G	SOT–23 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (Note 3) (I _C = -1.0 mA _{dc} , I _B = 0)	V _{(BR)CEO}	-25	-	Vdc
Collector–Base Breakdown Voltage (I _C = -10 μA _{dc} , I _E = 0)	V _{(BR)CBO}	-25	-	Vdc
Emitter–Base Breakdown Voltage (I _E = -10 μA _{dc} , I _C = 0)	V _{(BR)EBO}	-4	-	Vdc
Collector Cutoff Current (V _{CE} = -30 Vdc, V _{EB} = -3.0 Vdc)	I _{CEX}	-	-50	nA _{dc}
ON CHARACTERISTICS (Note 3)				
DC Current Gain (I _C = -2.0 mA _{dc} , V _{CE} = -1.0 Vdc) (I _C = -50 mA _{dc} , V _{CE} = -1.0 Vdc)	H _{FE}	120 60	300 -	-
Collector–Emitter Saturation Voltage (I _C = -50 mA _{dc} , I _B = -5.0 mA _{dc})	V _{CE(sat)}	-	-0.4	Vdc
Base–Emitter Saturation Voltage (I _C = -50 mA _{dc} , I _B = -5.0 mA _{dc})	V _{BE(sat)}	-	-0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current–Gain–Bandwidth Product (I _C = -10 mA _{dc} , V _{CE} = -20 Vdc, f = 100 MHz)	f _T	250	-	MHz
Output Capacitance (V _{CB} = -5.0 Vdc, I _E = 0, f = 1.0 MHz)	C _{obo}	-	4.5	pF
Input Capacitance (V _{EB} = -0.5 Vdc, I _C = 0, f = 1.0 MHz)	C _{ibo}	-	10	pF
Small–Signal Current Gain (I _C = -2.0 mA _{dc} , V _{CE} = -10 Vdc, f = 1.0 kHz) (I _C = 10 mA _{dc} , V _{CE} = 20 Vdc, f = 100 MHz)	h _{fe}	120 2.5	480 -	-
Noise Figure (I _C = -100 μA _{dc} , V _{CE} = -5.0 Vdc, R _S = 1.0 kΩ, f = 1.0 kHz)	NF	-	4.0	dB

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

TYPICAL TRANSIENT CHARACTERISTICS

— T_J = 25°C
 - - - T_J = 125°C

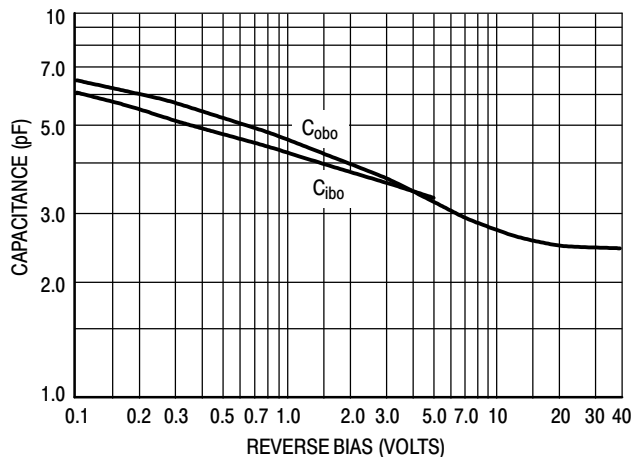


Figure 1. Capacitance

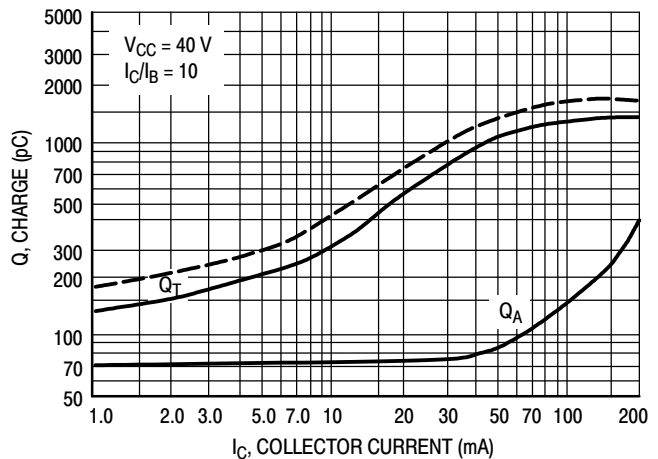


Figure 2. Charge Data

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TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

($V_{CE} = -5.0$ Vdc, $T_A = 25^\circ\text{C}$, Bandwidth = 1.0 Hz)

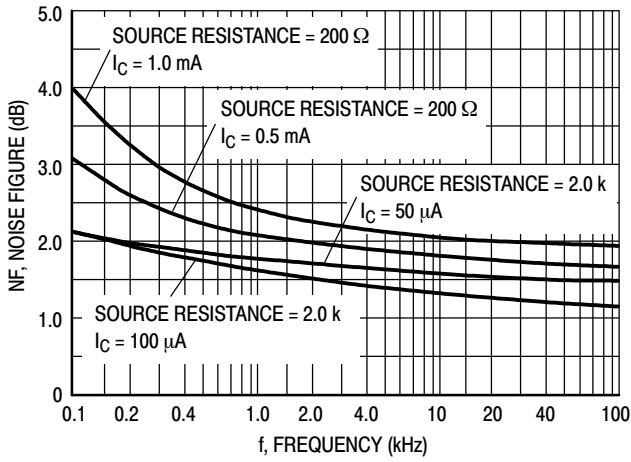


Figure 3.

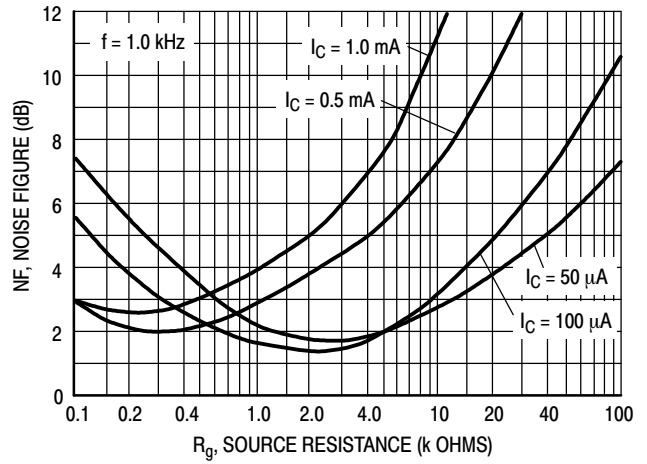


Figure 4.

h PARAMETERS

($V_{CE} = -10$ Vdc, $f = 1.0$ kHz, $T_A = 25^\circ\text{C}$)

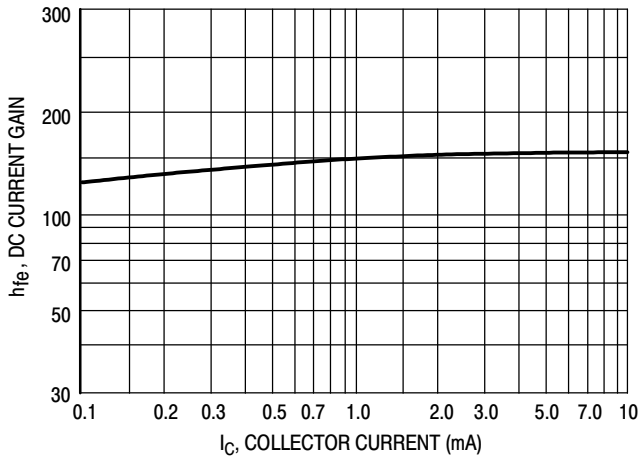


Figure 5. Current Gain

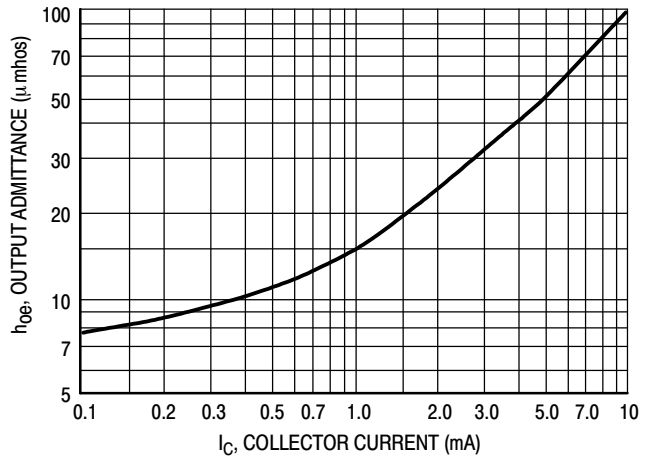


Figure 6. Output Admittance

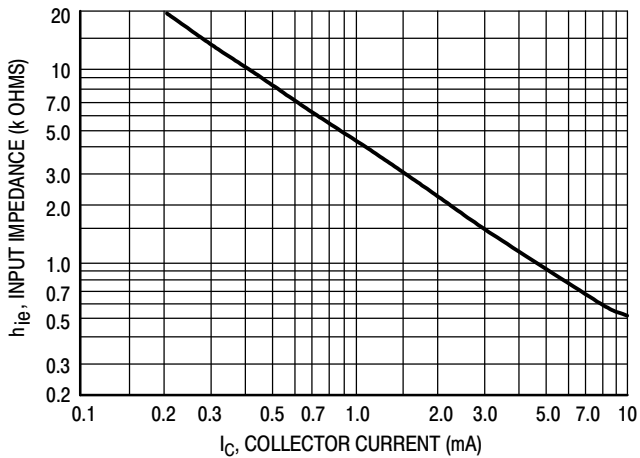


Figure 7. Input Impedance

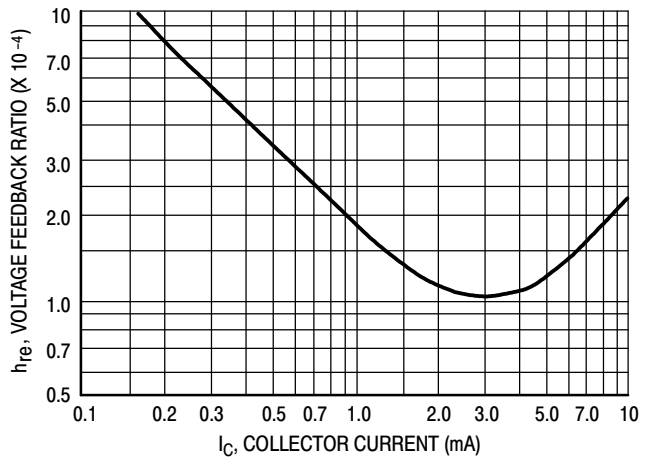


Figure 8. Voltage Feedback Ratio

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TYPICAL STATIC CHARACTERISTICS

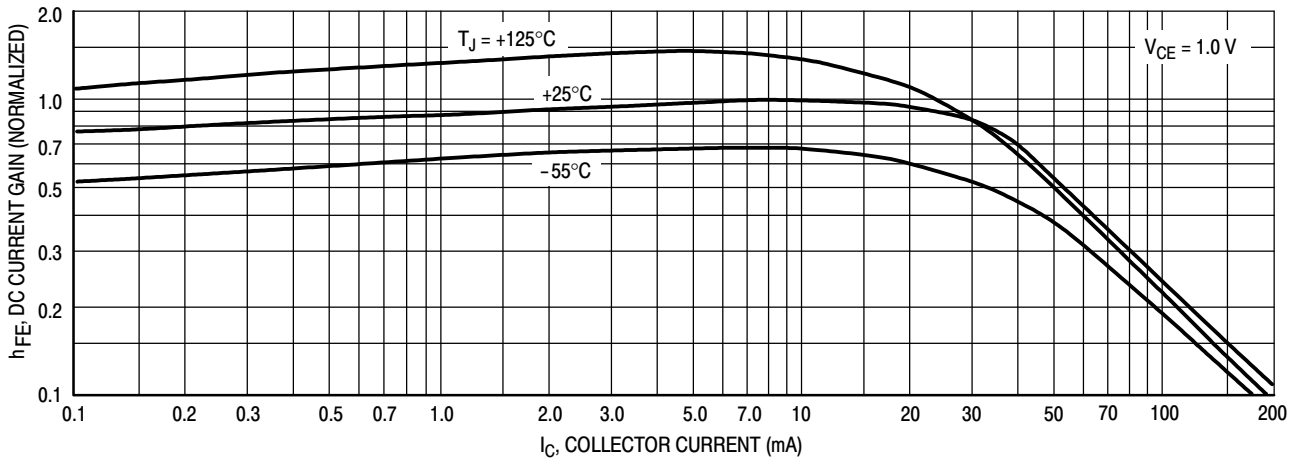


Figure 9. DC Current Gain

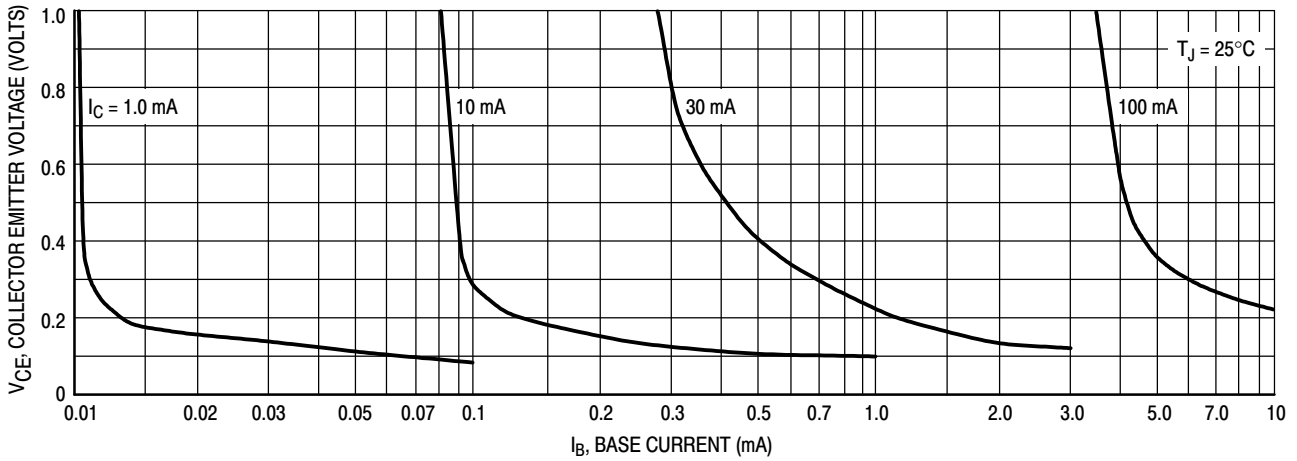


Figure 10. Collector Saturation Region

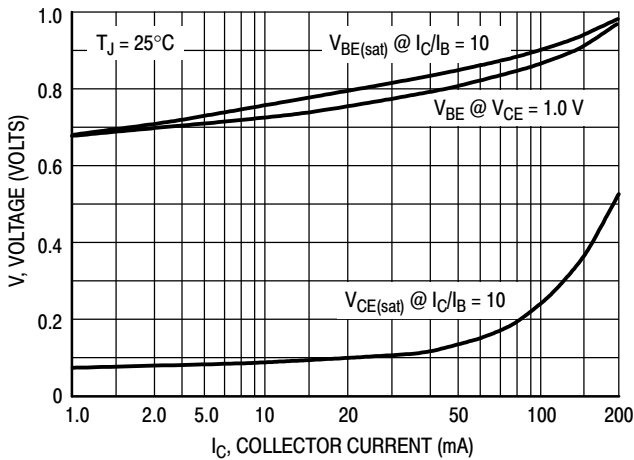


Figure 11. "ON" Voltages

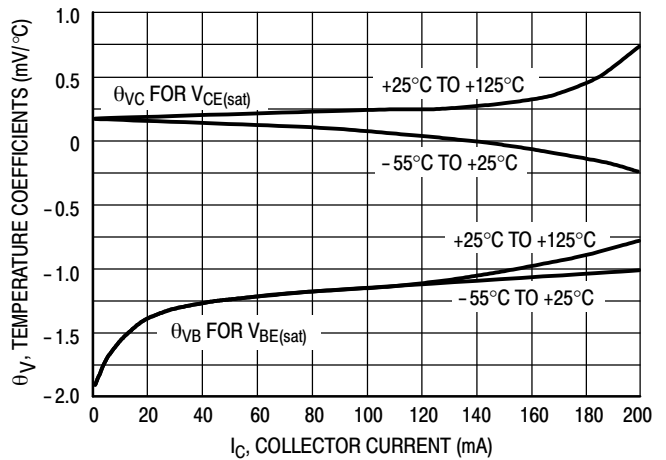
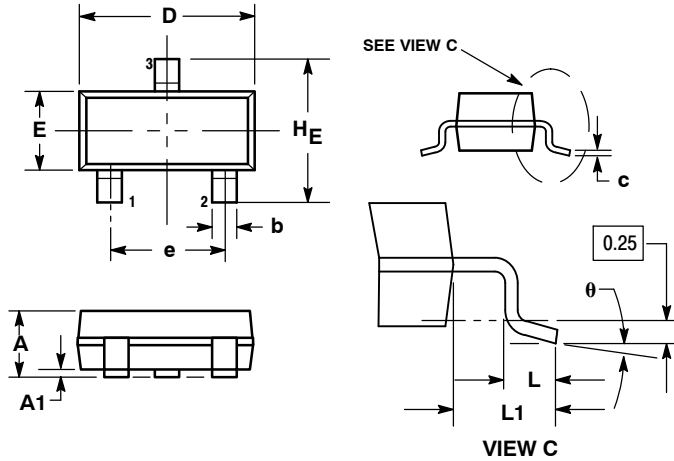


Figure 12. Temperature Coefficients

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PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AN



NOTES:

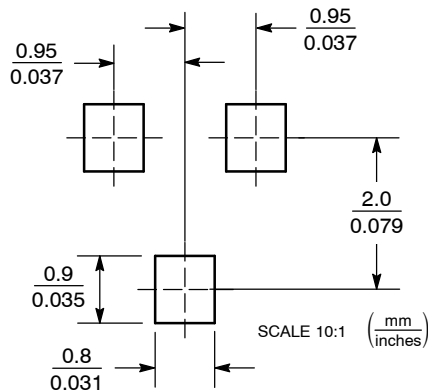
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 6:

1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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